



June 2015



FQB5N60CTM_WS

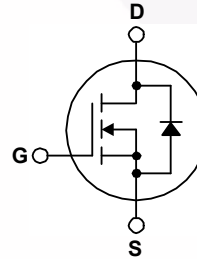
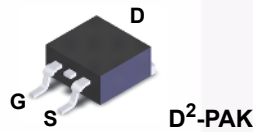
N-Channel QFET[®] MOSFET 600 V, 4.5 A, 2.5 Ω

Features

- 4.5 A, 600 V, $R_{DS(on)} = 2.5 \Omega$ (Max.) @ $V_{GS} = 10 V, I_D = 2.1 A$
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 6.5 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FQB5N60CTM_WS	Unit
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current - Continuous ($T_C = 25^\circ C$) - Continuous ($T_C = 100^\circ C$)	4.5	A
		2.6	A
I_{DM}	Drain Current - Pulsed (Note 1)	18	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	210	mJ
I_{AR}	Avalanche Current (Note 1)	4.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	10	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$) - Derate Above $25^\circ C$	100	W
		0.8	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	FQB5N60CTM_WS	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.25	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (1 in ² Pad of 2-oz Copper), Max.	40	

FQB5N60CTM_WS — N-Channel QFET[®] MOSFET

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB5N60CTM_WS	FQB5N60CS	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit	
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600	--	--	V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.6	--	$\text{V}/^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA	
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA	
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA	
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA	
On Characteristics							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.25\text{ A}$	--	2.0	2.5	Ω	
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 2.25\text{ A}$	--	4.7	--	S	
Dynamic Characteristics							
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	515	670	pF	
C_{oss}	Output Capacitance		--	55	72	pF	
C_{riss}	Reverse Transfer Capacitance		--	6.5	8.5	pF	
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 4.5\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 25\ \Omega$	--	10	30	ns	
t_r	Turn-On Rise Time		--	42	90	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	--	38	85	ns
t_f	Turn-Off Fall Time		(Note 4)	--	46	100	ns
Q_g	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 4.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	15	19	nC	
Q_{gs}	Gate-Source Charge		(Note 4)	--	2.5	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	6.6	--	nC
Drain-Source Diode Characteristics and Maximum Ratings							
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	4.5	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	18	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 4.5\text{ A}$	--	--	1.4	V	
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 4.5\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	300	--	ns	
Q_{rr}	Reverse Recovery Charge		--	2.2	--	μC	

NOTES:

1. Repetitive rating : pulse width limited by maximum junction temperature.
2. $L = 18.9\text{ mH}, I_{AS} = 4.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 4.5\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

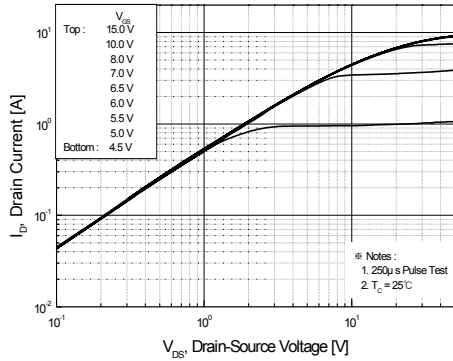


Figure 1. On-Region Characteristics

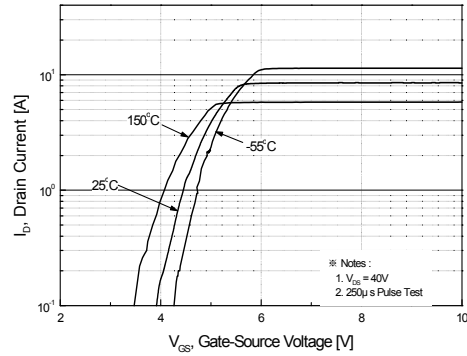


Figure 2. Transfer Characteristics

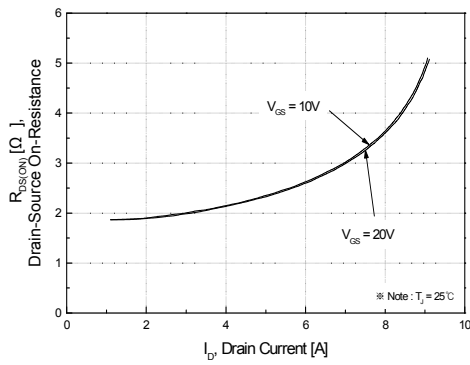


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

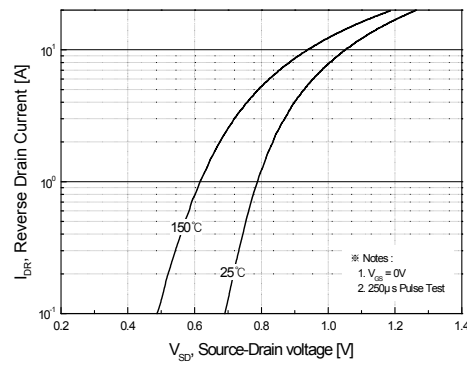


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

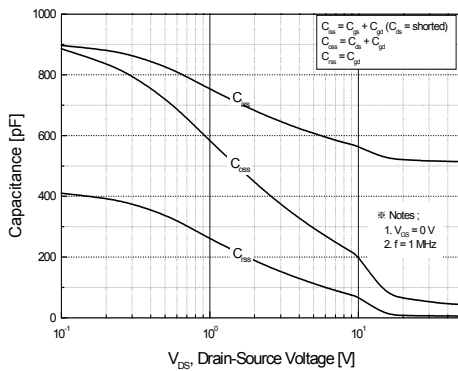


Figure 5. Capacitance Characteristics

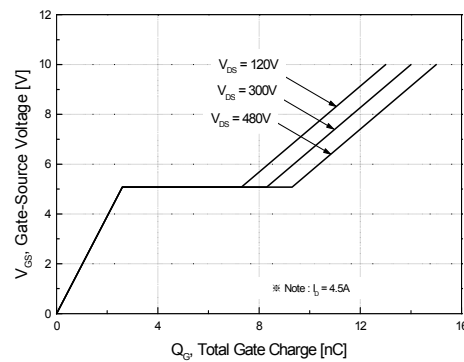


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

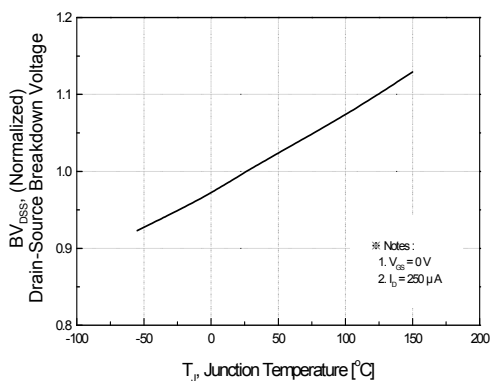


Figure 7. Breakdown Voltage Variation vs Temperature

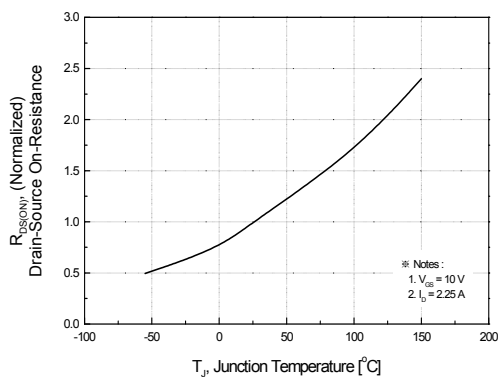


Figure 8. On-Resistance Variation vs Temperature

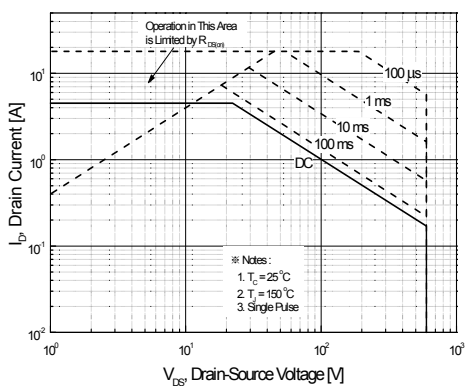


Figure 9. Maximum Safe Operating Area

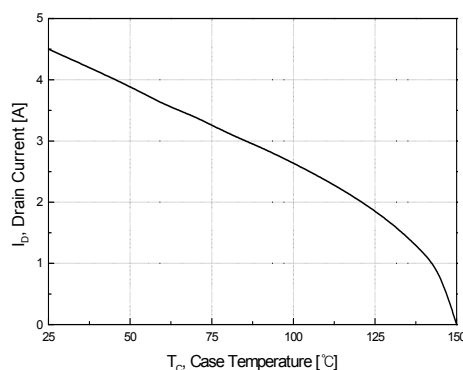


Figure 10. Maximum Drain Current vs Case Temperature

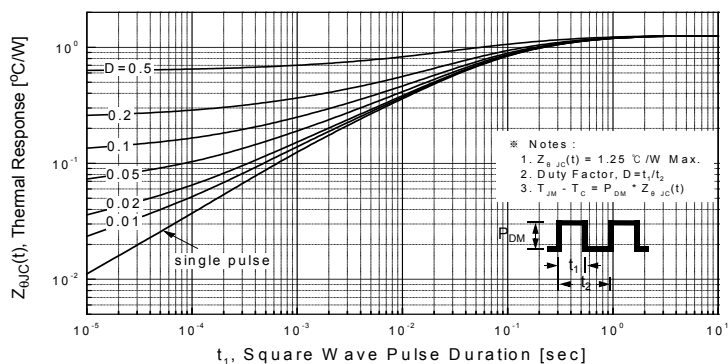


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

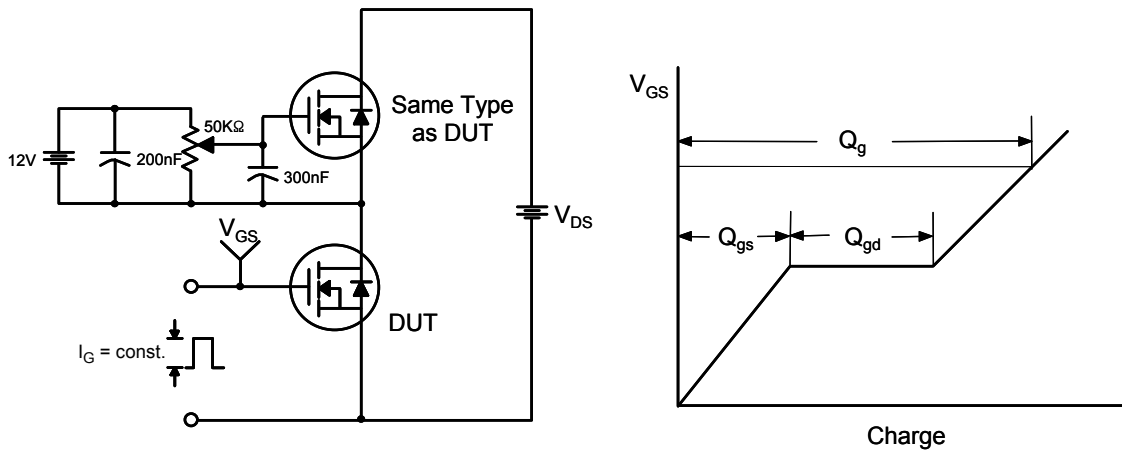


Figure 13. Resistive Switching Test Circuit & Waveforms

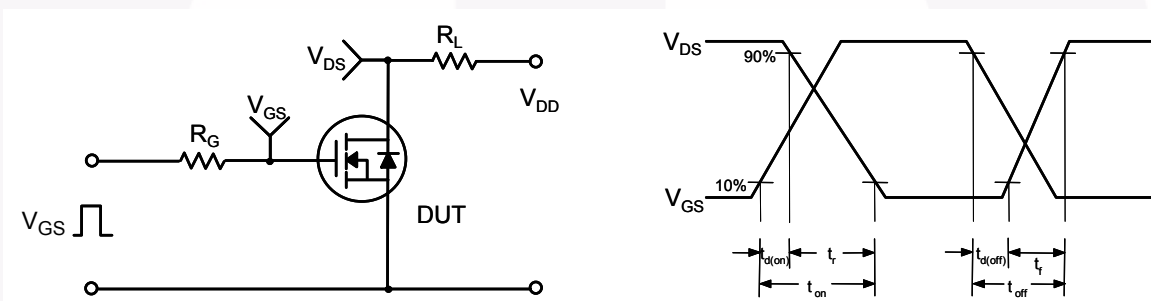


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

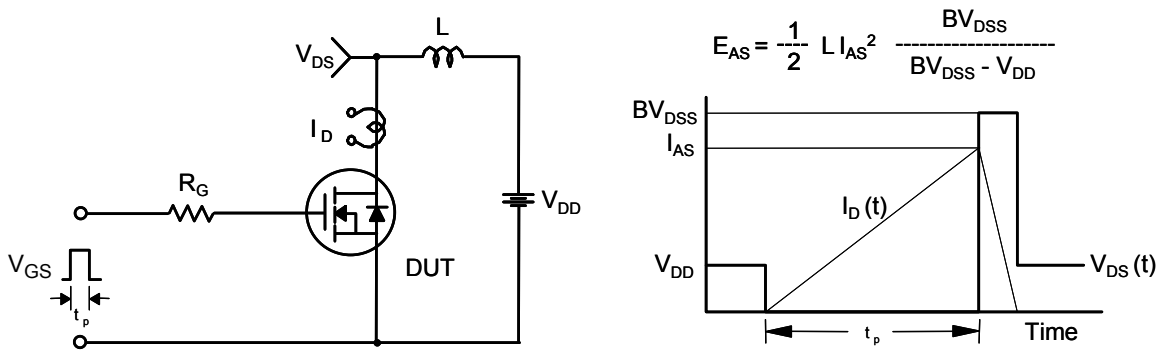
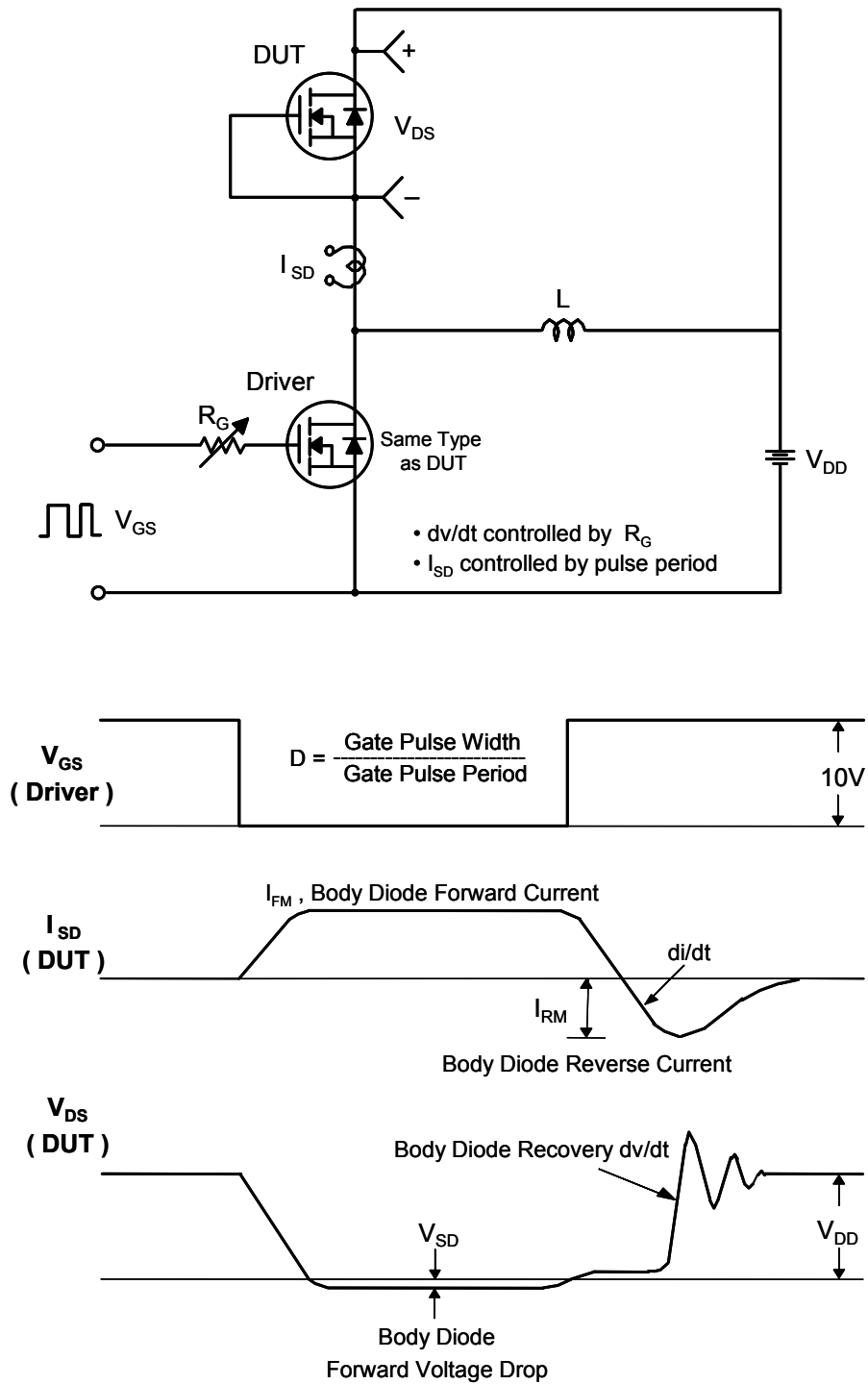
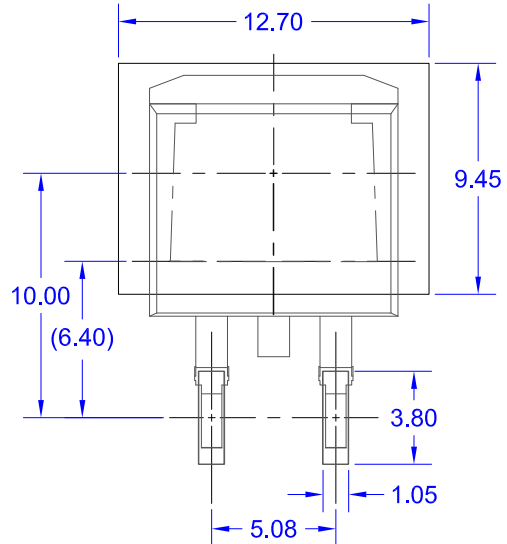
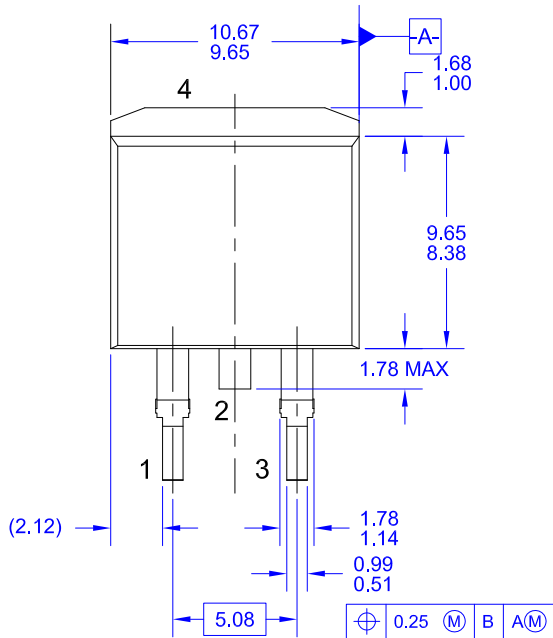
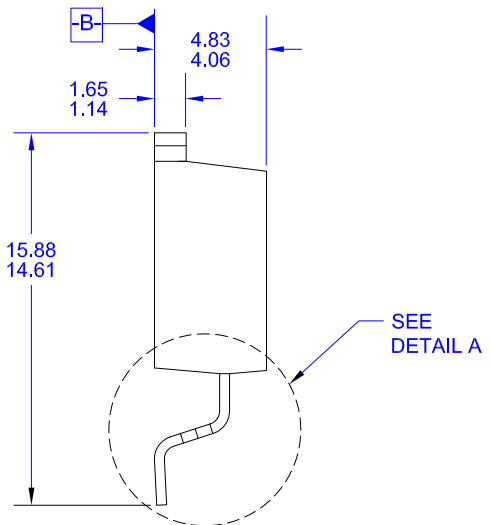
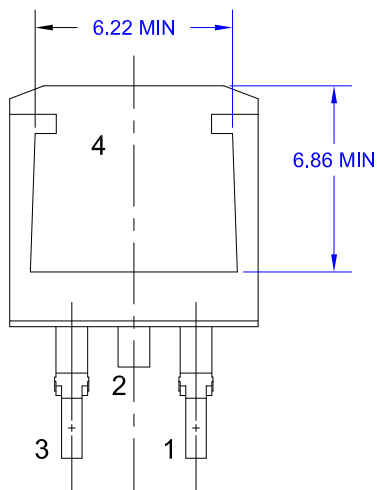


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

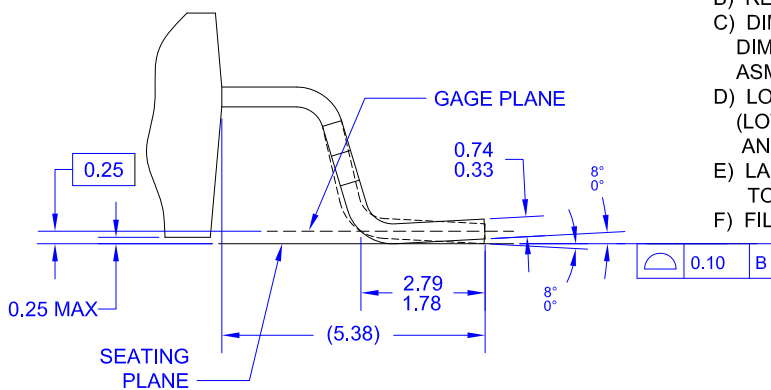




LAND PATTERN RECOMMENDATION
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- NOTES: UNLESS OTHERWISE SPECIFIED
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 B) REFERENCE JEDEC, TO-263, VARIATION AB.
 C) DIMENSIONING AND TOLERANCING PER DIMENSIONING AND TOLERANCING PER ASME Y14.5 - 2009.
 D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
 E) LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N
 F) FILENAME: TO263A02REV7



DETAIL A, ROTATED 90°
SCALE: 2X





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